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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/774,536	02/10/2004	Yuichi Sato	204552016501	3216	
75	90 02/07/2005		EXAM	EXAMINER	
Barry E. Bretschneider Morrison & Foerster LLP Suite 300 1650 Tysons Boulevard McLean, VA 22102			WILLE, DOUGLAS A		
			ART UNIT	PAPER NUMBER	
			2814		
			DATE MAILED: 02/07/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)				
Office Action Summary		10/774,536	SATO, YUICHI				
		Examiner	Art Unit				
		Douglas A. Wille	2814				
Period fo	The MAILING DATE of this communication a or Reply	ppears on the cover sheet with	the correspondence address				
A SH THE - Exte after - If the - If NO - Faill Any	ORTENED STATUTORY PERIOD FOR REF MAILING DATE OF THIS COMMUNICATION insions of time may be available under the provisions of 37 CFR SIX (6) MONTHS from the mailing date of this communication. It is period for reply specified above is less than thirty (30) days, a reperiod for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by state reply received by the Office later than three months after the mailed patent term adjustment. See 37 CFR 1.704(b).	N. 1.136(a). In no event, however, may a reply eply within the statutory minimum of thirty (3) od will apply and will expire SIX (6) MONTHS ute, cause the application to become ABANI	be timely filed 0) days will be considered timely. 6 from the mailing date of this communication. DONED (35 U.S.C. § 133).				
Status							
1) 又	Responsive to communication(s) filed on 10	February 2004.					
'=	This action is FINAL . 2b)⊠ This action is non-final.						
3)□	,—						
.—	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposit	ion of Claims						
4)🖂	Claim(s) <u>1-9</u> is/are pending in the application.						
,	4a) Of the above claim(s) is/are withdrawn from consideration.						
5)	Claim(s) is/are allowed.						
6)⊠	Claim(s) 1-9 is/are rejected.						
7)	Claim(s) is/are objected to.						
	Claim(s) are subject to restriction and/or election requirement.						
Applicat	ion Papers						
9) The specification is objected to by the Examiner.							
• —	☑ The drawing(s) filed on 10 February 2004 is/are: a)☑ accepted or b)☐ objected to by the Examiner.						
,—	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
	Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11)	11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority (under 35 U.S.C. § 119						
,	Acknowledgment is made of a claim for foreign All b) Some * c) None of: 1. Certified copies of the priority docume		19(a)-(d) or (f).				
	Certified copies of the priority documents have been received in Application No						
	3. Copies of the certified copies of the pr	• •					
	application from the International Bure	<u> </u>					
* (See the attached detailed Office action for a li	st of the certified copies not rec	ceived.				
Attachmer		П					
1) Notice of References Cited (PTO-892) 4) Interview Summary (PTO-413) Paper No(s)/Mail Date							
3) 🛛 Infor	mation Disclosure Statement(s) (PTO-1449 or PTO/SB/0er No(s)/Mail Date 0204.		mal Patent Application (PTO-152)				

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. Claims 1, 2 and 4 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's admitted prior art and Hu et al.
- 2. With respect to claim 1, Applicant's admitted prior art, Figure 9, shows an SRAM comprised of CMOS devices. Hu et al. show a DTMOS device (see Figure 7 and column 1, line 8 et seq.) that has the n-well deeper than the p-well and that can be used in CMOS circuitry for the advantages shown (column 2, line 46). It would have been obvious to modify the basic device to include the DTMOS device shown by Hu et al. for the advantages shown. Note that the gates are electrically connected.
- 3. With respect to claim 2, note that the gates of the devices are connected to a power supply and therefore, so are the channel forming regions.
- 4. With respect to claim 4, Hu et al. show a DTMOS device (see Figure 7 and column 1, line 8 et seq.) that has the n-well deeper than the p-well.
- 5. Claim 3 is rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's admitted prior art and Hu et al. and further in view of Tsui et al.
- 6. Tsui et al. show the use of dual thickness gate oxides with thinner gate oxides used for low voltage devices (column 1, line 14). Since DTMOS devices use lower voltages it would have been obvious to use thinner oxides for the lower voltage devices and to use normal gate oxides for other devices.
- 7. Claims 5, 6 and 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's admitted prior art and Hu et al. and further in view of Hodges et al.

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- 8. With respect to claim 5, Hodges et al. show the formation of peripheral circuits for a memory device that use MOS structures (see page 368 and 369) and it would be obvious to use the DTMOS devices for these structures for the advantages shown.
- 9. With respect to claim 6, bit lines are shown.
- 10. With respect to claim 9, Hu et al. show a DTMOS device (see Figure 7 and column 1, line 8 et seq.) that has the n-well deeper than the p-well.
- 11. Claim 8 is rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's admitted prior art and Hu et al. and further in view of Hodges.
- 12. Hodges shows a SRAM which uses resistors as an alternative SRAM to that shown in Applicant's admitted prior art (see cover Figure) and it would be obvious to use that circuit as a design choice and to use the DTMOS devices for the advantages shown.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Douglas A. Wille whose telephone number is (571) 272-1721. The examiner can normally be reached on M-F (6:15-2:45).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (703) 308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9306 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

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Loresta LOULLI
Douglas A. Wille
Patent Examiner